MSD602-RT1

Preferred Device

NPN General Purpose Amplifier Transistor Surface Mount

ON Semiconductor®

http://onsemi.com

Features

- Pb−Free Packages are Available

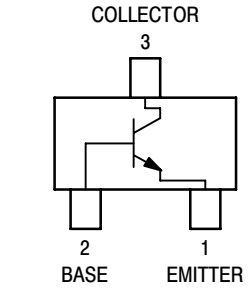
MAXIMUM RATINGS (T_A = 25°C)

Rating	Symbol	Value	Unit
Collector−Base Voltage	$V_{(BR)CBO}$	60	Vdc
Collector−Emitter Voltage	$V_{(BR)CEO}$	50	Vdc
Emitter−Base Voltage	$V_{(BR)EBO}$	7.0	Vdc
Collector Current − Continuous	I_C	500	mAdc
Collector Current − Peak	$I_{C(P)}$	1.0	Adc

THERMAL CHARACTERISTICS

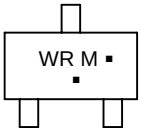
Characteristic	Symbol	Max	Unit
Power Dissipation	P_D	200	mW
Junction Temperature	T_J	150	°C
Storage Temperature	T_{stg}	−55 ~ +150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.



MARKING DIAGRAM

SC−59
CASE 318D



WR = Specific Device Code
M = Date Code
▪ = Pb−Free Package
(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

ELECTRICAL CHARACTERISTICS (T_A = 25°C)

Characteristic	Symbol	Min	Max	Unit
Collector−Emitter Breakdown Voltage (I_C = 10 mAdc, I_B = 0)	$V_{(BR)CEO}$	50	−	Vdc
Collector−Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	$V_{(BR)CBO}$	60	−	Vdc
Emitter−Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	7.0	−	Vdc
Collector−Base Cutoff Current (V_{CB} = 20 Vdc, I_E = 0)	I_{CBO}	−	0.1	μAdc
DC Current Gain (Note 1) (V_{CE} = 10 Vdc, I_C = 150 mAdc) (V_{CE} = 10 Vdc, I_C = 500 mAdc)	h_{FE1} h_{FE2}	120 40	240 —	−
Collector−Emitter Saturation Voltage (I_C = 300 mAdc, I_B = 30 mAdc)	$V_{CE(sat)}$	−	0.6	Vdc
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)	C_{ob}	−	15	pF

1. Pulse Test: Pulse Width ≤ 300 μs, D.C. ≤ 2%.

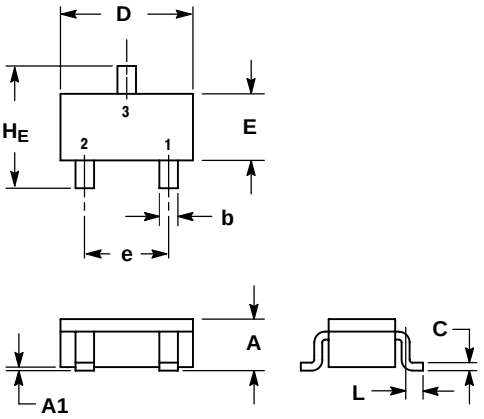
ORDERING INFORMATION

Device	Package	Shipping†
MSD−602RT1	SC−59	3000 Units / Reel
MSD−602RT1G	SC−59 (Pb−Free)	3000 Units / Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

SC−59
CASE 318D−04
ISSUE G

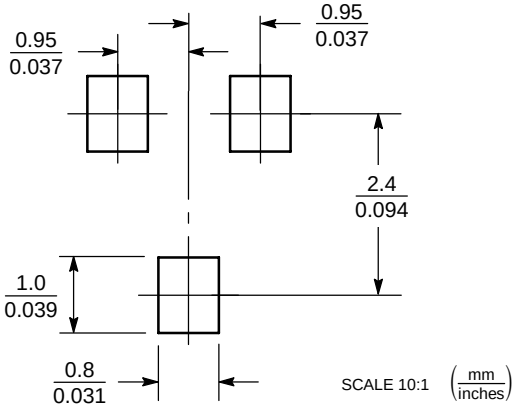


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	1.00	1.15	1.30	0.039	0.045	0.051
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.35	0.43	0.50	0.014	0.017	0.020
c	0.09	0.14	0.18	0.003	0.005	0.007
D	2.70	2.90	3.10	0.106	0.114	0.122
E	1.30	1.50	1.70	0.051	0.059	0.067
e	1.70	1.90	2.10	0.067	0.075	0.083
L	0.20	0.40	0.60	0.008	0.016	0.024
H_E	2.50	2.80	3.00	0.099	0.110	0.118

STYLE 1:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 61312, Phoenix, Arizona 85082−1312 USA
Phone: 480−829−7710 or 800−344−3860 Toll Free USA/Canada
Fax: 480−829−7709 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada

Japan: ON Semiconductor, Japan Customer Focus Center
2−9−1 Kamimeguro, Meguro−ku, Tokyo, Japan 153−0051
Phone: 81−3−5773−3850

ON Semiconductor Website: http://onsemi.com

Order Literature: http://www.onsemi.com/litorder

For additional information, please contact your local Sales Representative.